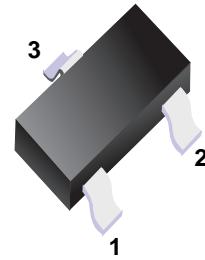
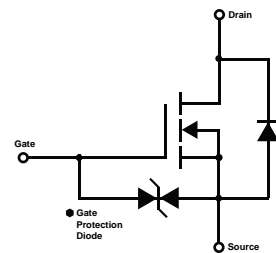


**■ N-channel MOSFET**
**■ FEATURES**

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for portable equipment
- Easily designed drive circuits
- Easy to parallel


 1.GATE  
 2.SOURCE  
 3.DRAIN

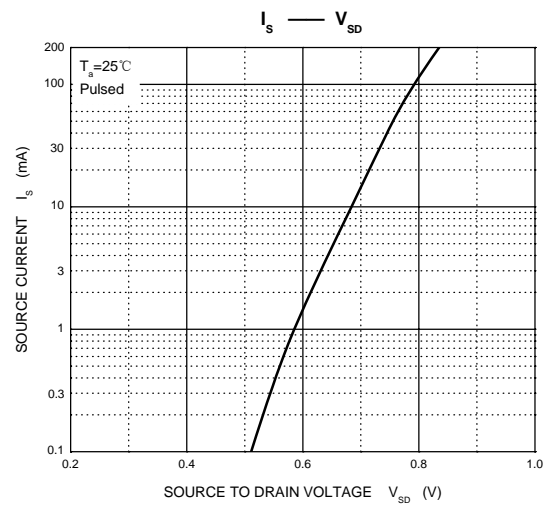
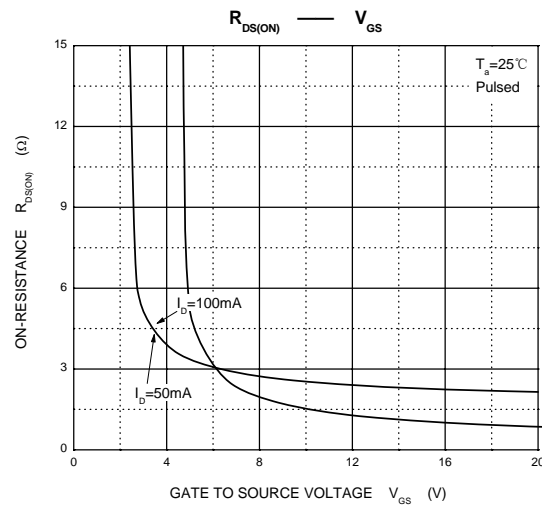
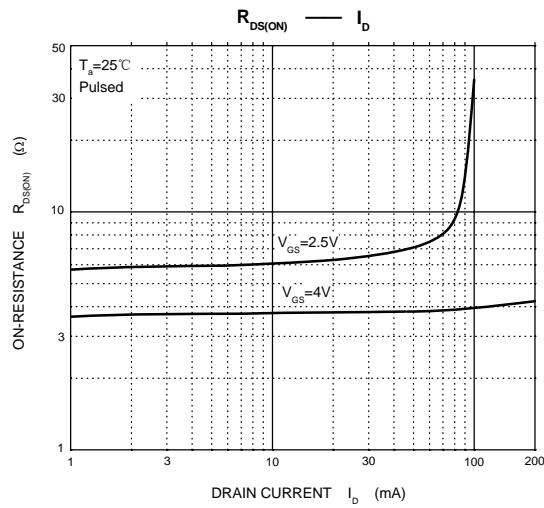
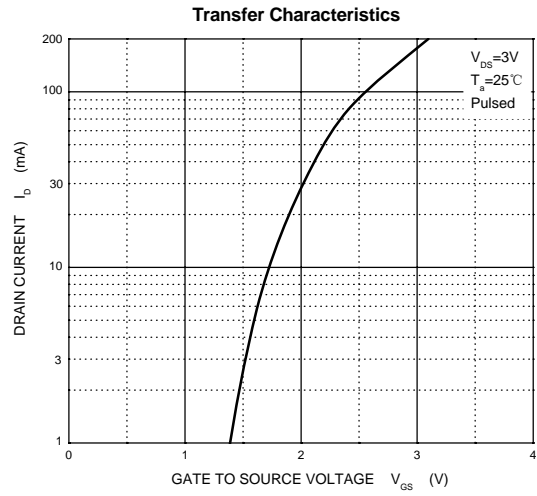
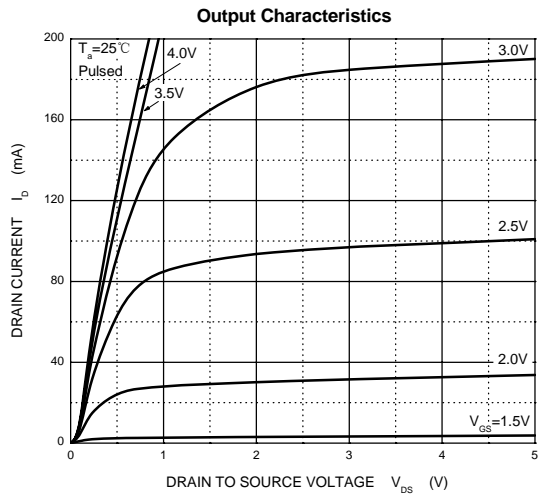
**■ Simplified outline(SOT-523)**
**Equivalent circuit**

**■ MOSFET MAXIMUM RATINGS (Ta = 25°C unless otherwise noted)**

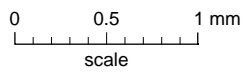
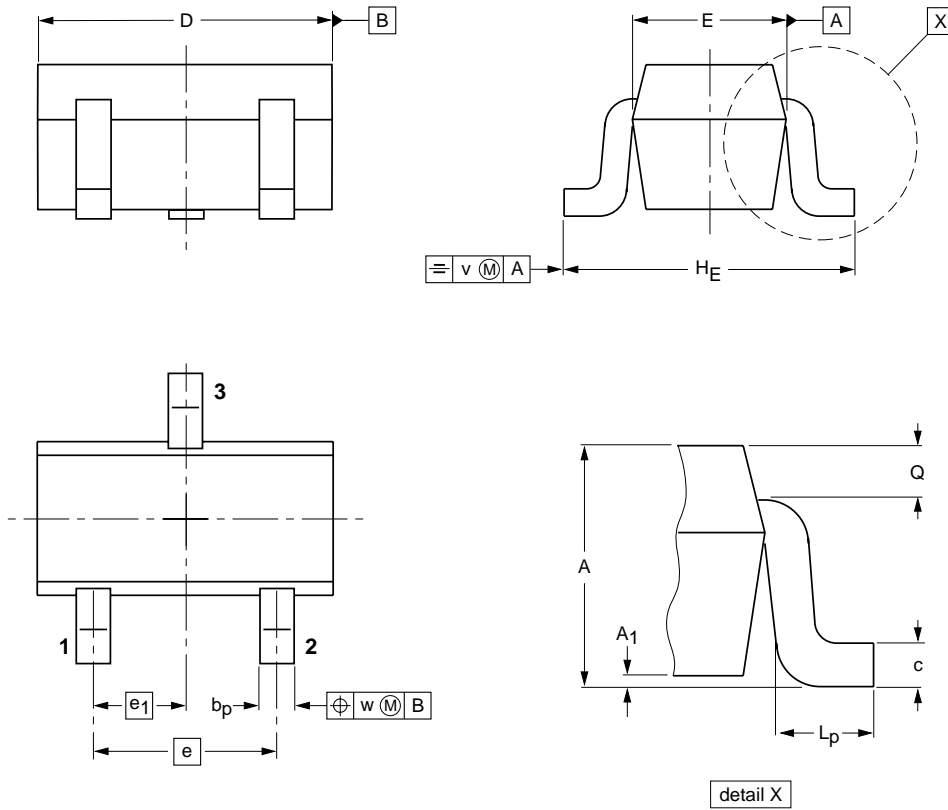
Symbol	Parameter	Value	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Continuous Drain Current	0.1	A
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	833	°C /W
P <sub>D</sub>	Power Dissipation	0.15	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

**■ MOSFET ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA	30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> = 0V			1	μA
Gate –Source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> = 0V			±1	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = 3V, I <sub>D</sub> =100μA	0.8		1.5	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4V, I <sub>D</sub> =10mA			8	Ω
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1mA			13	Ω
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =3V, I <sub>D</sub> = 10mA	20			mS
<b>Dynamic Characteristics*</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =5V, V <sub>GS</sub> =0V, f =1MHz		13		pF
Output Capacitance	C <sub>oss</sub>			9		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			4		pF
<b>Switching Characteristics*</b>						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> =5V, V <sub>DD</sub> =5V, I <sub>D</sub> =10mA, R <sub>g</sub> =10Ω, R <sub>L</sub> =500Ω,		15		ns
Rise Time	t <sub>r</sub>			35		ns
Turn-Off Delay Time	t <sub>d(off)</sub>			80		ns
Fall Time	t <sub>f</sub>			80		ns

\* These parameters have no way to verify.



**■ SOT-523**

**DIMENSIONS (mm are the original dimensions)**

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2